

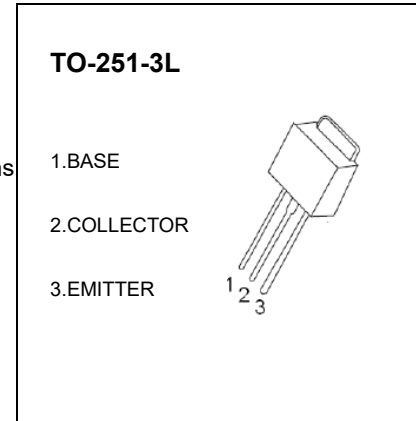


# JSCJ TO-251-3L Plastic-Encapsulate Transistors

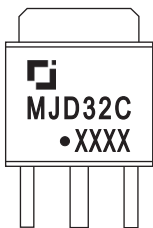
## MJD32C TRANSISTOR (PNP)

### FEATURES

- Designed for General Purpose Amplifier and Low Speed Switching Applications
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series

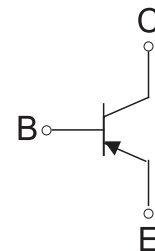


### MARKING



MJD32C=Device code  
 Solid dot=Green moldinn compound device,  
 if none,the normal device  
 XXXX=Code

### Equivalent Circuit



### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

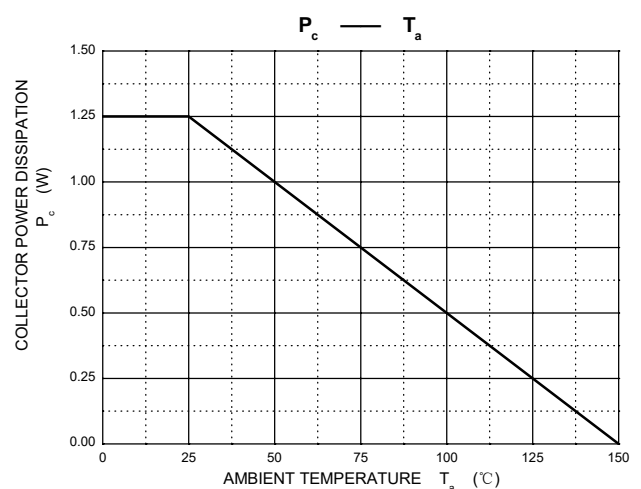
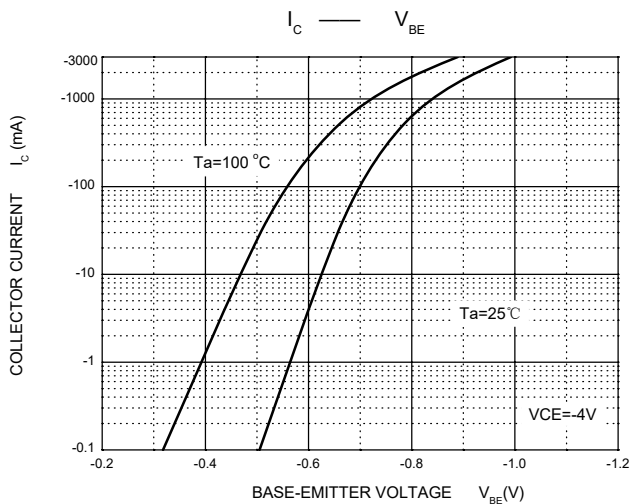
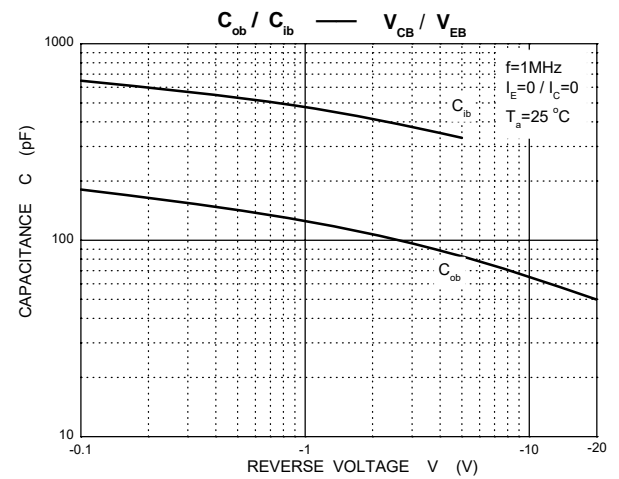
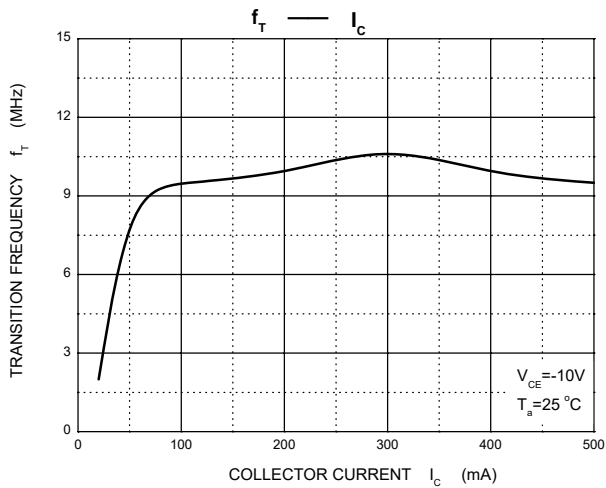
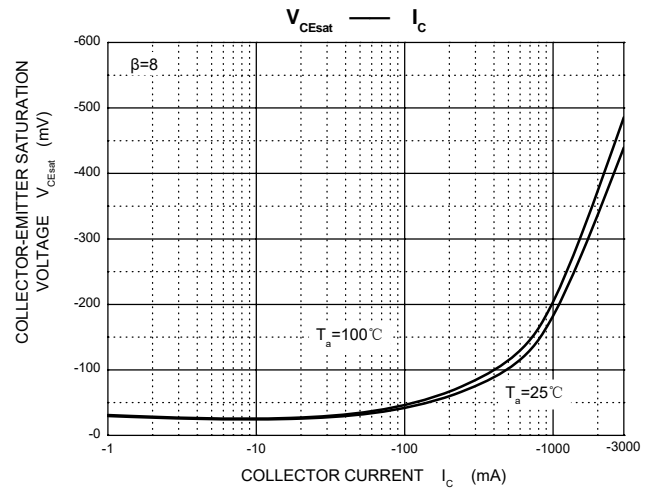
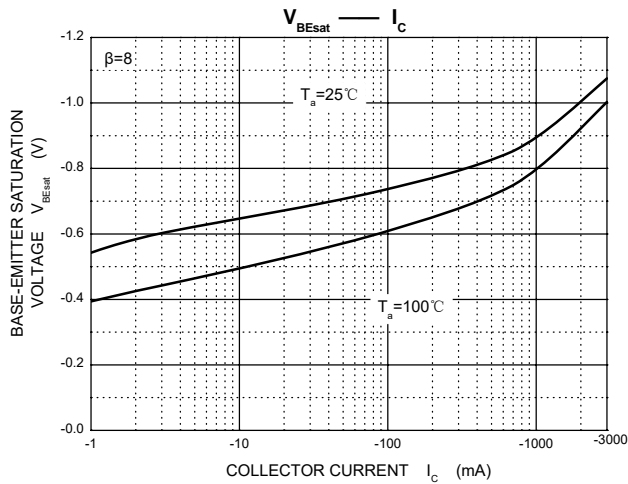
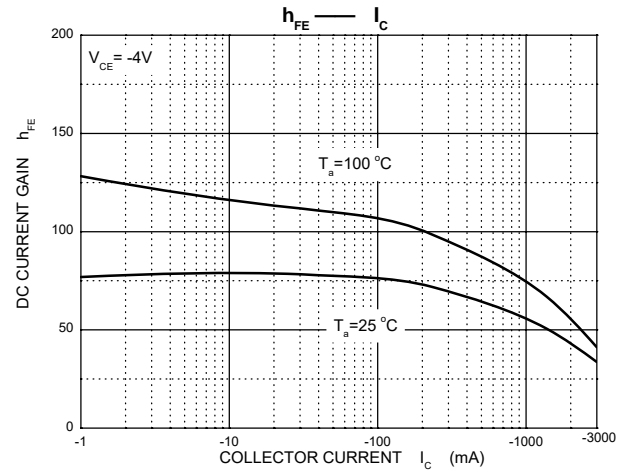
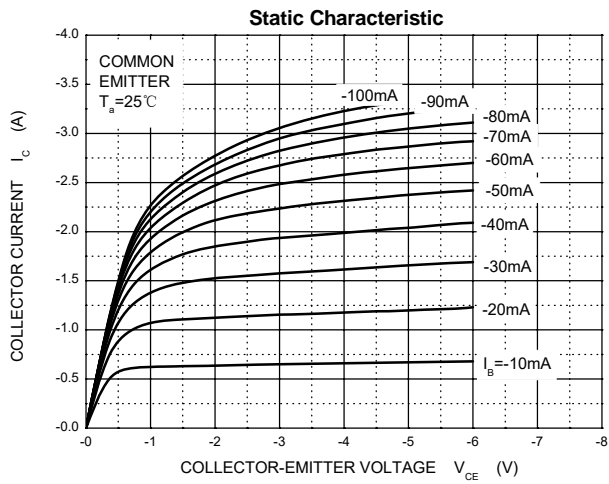
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>c</sub>	Collector Current -Continuous	-3	A
P <sub>c</sub>	Collector Power Dissipation	1.25	W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

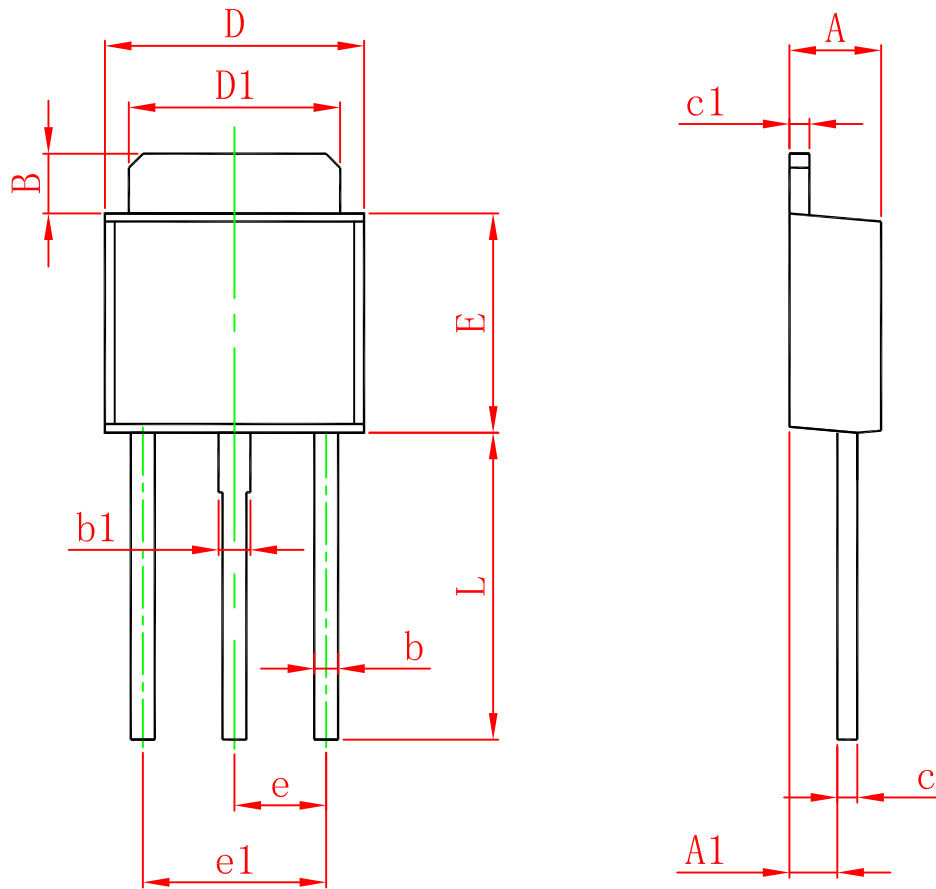
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -1mA, I <sub>E</sub> =0	-100		V
Collector-emitter breakdown voltage *	V <sub>CEO(sus)</sub>	I <sub>C</sub> = -30mA, I <sub>B</sub> =0	-100		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CES</sub>	V <sub>CE</sub> =-100V, V <sub>EB</sub> =0		-2	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -60V, I <sub>B</sub> = 0		-5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-1	mA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -4V, I <sub>C</sub> =-1A	25		
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-4 V, I <sub>C</sub> =-3A	15	75	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-3A, I <sub>B</sub> =-0.375A		-1.2	V
Base-emitter voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = -4V, I <sub>C</sub> =-3A		-1.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-0.5A, f <sub>T</sub> =1kHz	3		MHz

\* Pulse Test: PW≤300μs, Duty Cycle≤2%.

# Typical Characteristics



# TO-251-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311